General purpose transistor (isolated transistor and diode)

QSZ4

A 2SB1706 and a 2SD2671 are housed independently in a TSMT5 package.

Applications

DC / DC converter Motor driver

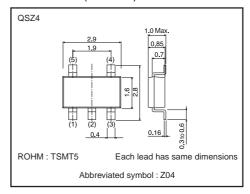
● Features

- 1) Low VcE(sat)
- 2) Small package

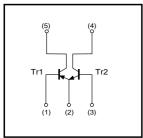
●Structure

Silicon epitaxial planar transistor

●Dimensions (Unit: mm)



●Equivalent circuit



Packaging specifications

Туре	QSZ4
Package	TSMT5
Marking	Z04
Code	TR
Basic ordering unit(pieces)	3000

Rev.B

● Absolute maximum ratings (Ta=25°C)

Tr1

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	-30	V
Collector-emitter voltage	Vceo	-30	V
Emitter-base voltage	Vево	-6	V
Collector current	lc	-2	А
	Іср	-4	A *1
		500	mW/Total *2
Power dissipation	Pc	1.25	W/Total *3
		0.9	W/Element *3
Junction temperature	Tj	150	°C
Range of storage temperature	Tstg	-55 to +150	°C

Tr 2

Parameter	Symbol	Limits	Unit
Collector-base voltage	Vсво	30	V
Collector-emitter voltage	Vceo	30	V
Emitter-base voltage	Vево	6	V
Collector current	Ic	2	Α
	Іср	4	A *1
Power dissipation		500	mW/Total *2
	Pc	1.25	W/Total *3
		0.9	W/Element *3
Junction temperature	Tj	150	°C
Range of storage temperature	Tstg	-55 to +150	°C

●Electrical characteristics (Ta=25°C)

Tr1

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	-30	-	_	V	Ic=-10μA
Collector-emitter breakdown voltage	BVceo	-30	-	-	V	Ic=-1mA
Emitter-base breakdown voltage	ВVево	-6	-	-	V	I _E = -10μA
Collector cutoff current	Ісво	_	-	-100	nA	Vcb=-30V
Emitter cutoff current	Ієво	-	-	-100	nA	V _{EB} = -6V
Collector-emitter saturation voltage	VCE(sat)	_	-180	-370	mV	Ic= -1.5A, I _B = -75mA
DC current gain	hfe	270	-	680	-	Vce= -2V, Ic= -200mA*
Transition frequency	f⊤	-	280	-	MHz	Vc=-2V, I=200mA, f=100MHz*
Collector output capacitance	Cob	-	20	-	pF	Vсв= −10V, I∈=0A, f=1MHz
* Bulcod				•		

^{*} Pulsed

Tr 2

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	30	-	_	V	Ic=10μA
Collector-emitter breakdown voltage	BVceo	30	_	_	V	Ic=1mA
Emitter-base breakdown voltage	ВVево	6	-	_	V	I _E =10μA
Collector cutoff current	Ісво	-	-	100	nA	Vcb=30V
Emitter cutoff current	ІЕВО	_	-	100	nA	V _{EB} =6V
Collector-emitter saturation voltage	VCE(sat)	_	180	370	mV	Ic=1.5A, Iв=75mA
DC current gain	hfe	270	-	680	-	Vce=2V, Ic=200mA*
Transition frequency	f⊤	_	280	_	MHz	Vce=2V, Ie= -200mA, f=100MHz*
Collector output capacitance	Cob	-	20	_	pF	Vcb=10V, Ie=0A, f=1MHz

^{*} Pulsed



^{*1} Single pulse, Pw=1ms.
*2 Each terminal mounted on a recommended land.
*3 Mounted on a 25×25× to.8mm ceramic substrate.

^{*1} Single pulse, Pw=1ms.
*2 Each terminal mounted on a recommended land.
*3 Mounted on a 25×25× 10.8mm ceramic substrate.

•Electrical characteristic curves

Tr1(PNP)

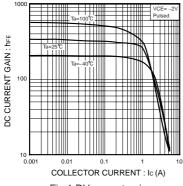


Fig.1 DV current gain vs. collector current

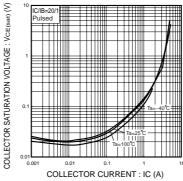


Fig.2 Collector-emitter saturation voltage vs. collector current

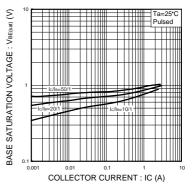


Fig.3 Base-emitter saturation voltage vs. collectir current

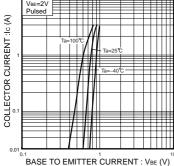


Fig.4 Grounded emitter propagation characteristics

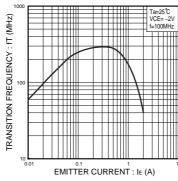
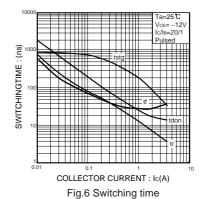


Fig.5 Gain bandwidth product vs. emitter curent



1000 | IC=OA | I=1MHz | Ta=25°C | IC=OA | IC=O

Fig.7 Collector output capacitance vs. collector-base voltage Emitter input capacitance vs. emitter-base voltage

Tr2(NPN)

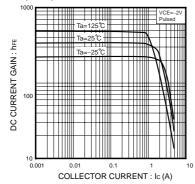


Fig.8 DC current gain vs. collector current

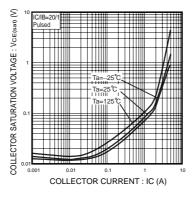


Fig.9 Collector-emitter saturation voltage base-emitter saturation voltage vs. collector current

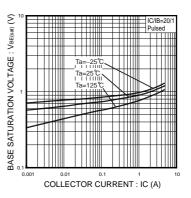


Fig.10 Base-emitter saturation voltage vs. collector current

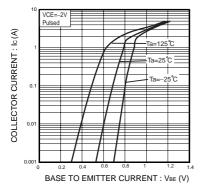


Fig.11 Grounded emitter propagation characteristics

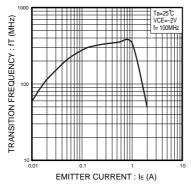


Fig.12 Gain bandwidth product vs. emitter current

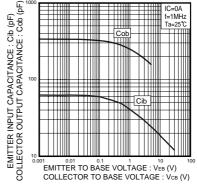


Fig.13 Collector output chapacitance vs. collector-base voltage Emitter input capacitance vs. emitter-base voltage

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